



# SPP1433

## P-Channel Enhancement Mode MOSFET

### DESCRIPTION

The SPP1433 is the P-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology.

This high density process is especially tailored to minimize on-state resistance.

These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits where high-side switching , and low in-line power loss are needed in a very small outline surface mount package.

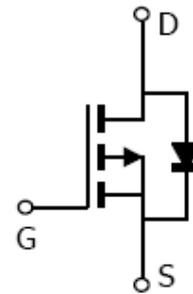
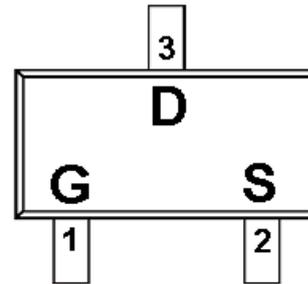
### FEATURES

- ◆ -30V/-2.8A, $R_{DS(ON)}=110m\Omega@V_{GS}=-10V$
- ◆ -30V/-2.5A, $R_{DS(ON)}=140m\Omega@V_{GS}=-4.5V$
- ◆ Super high density cell design for extremely low  $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOT-323 ( SC-70 ) package design

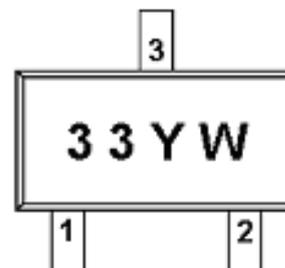
### APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

### PIN CONFIGURATION ( SOT-323 ; SC-70 )



### PART MARKING



Y : Year Code  
W : Week Code



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### PIN DESCRIPTION

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

### ORDERING INFORMATION

Part Number	Package	Part Marking
SPP1433S32RG	SOT-323	33YW
SPP1433S32RGB	SOT-323	33YW

- ※ Week Code : A ~ Z ( 1 ~ 26 ) ; a ~ z ( 27 ~ 52 )
- ※ SPP1433S32RG : Tape Reel ; Pb – Free
- ※ SPP1433S32RGB : Tape Reel ; Pb – Free ; Halogen - Free

### ABSOLUTE MAXIMUM RATINGS

( $T_A=25^{\circ}\text{C}$  Unless otherwise noted)

Parameter	Symbol	Typical	Unit	
Drain-Source Voltage	$V_{DSS}$	-30	V	
Gate –Source Voltage	$V_{GSS}$	$\pm 20$	V	
Continuous Drain Current( $T_J=150^{\circ}\text{C}$ )	$I_D$	$T_A=25^{\circ}\text{C}$	-2.8	A
		$T_A=70^{\circ}\text{C}$	-2.1	
Pulsed Drain Current	$I_{DM}$	-8	A	
Continuous Source Current(Diode Conduction)	$I_S$	-1.4	A	
Power Dissipation	$P_D$	$T_A=25^{\circ}\text{C}$	0.33	W
		$T_A=70^{\circ}\text{C}$	0.21	
Operating Junction Temperature	$T_J$	-55/150	$^{\circ}\text{C}$	
Storage Temperature Range	$T_{STG}$	-55/150	$^{\circ}\text{C}$	
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	105	$^{\circ}\text{C}/\text{W}$	



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### ELECTRICAL CHARACTERISTICS

( $T_A=25^\circ\text{C}$  Unless otherwise noted)

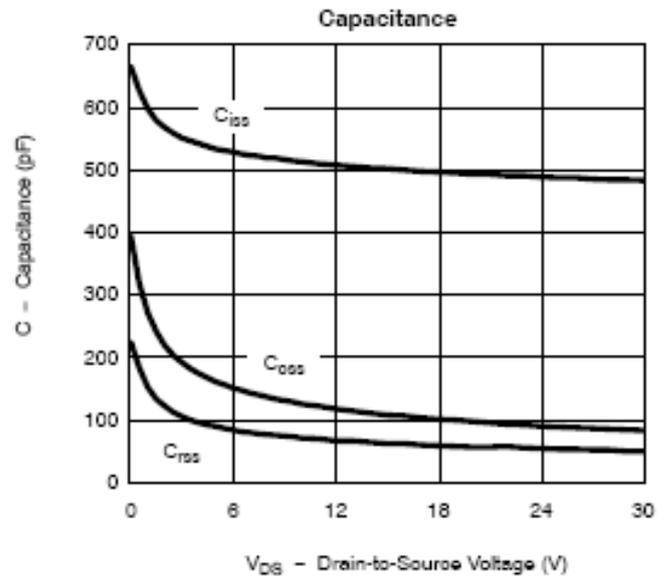
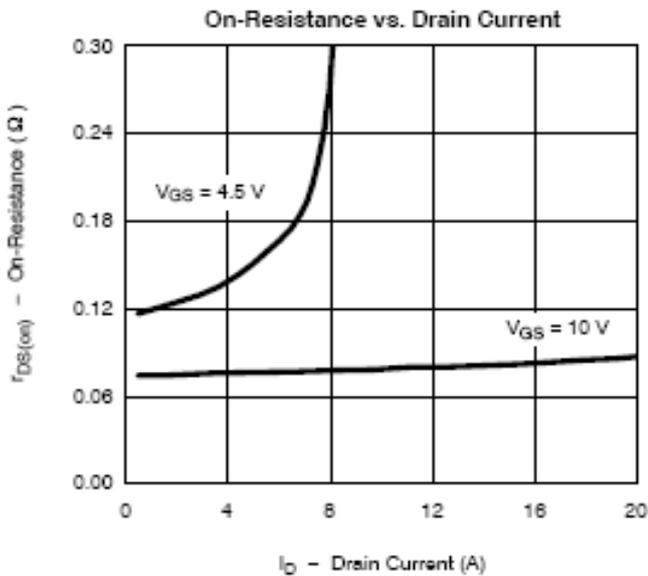
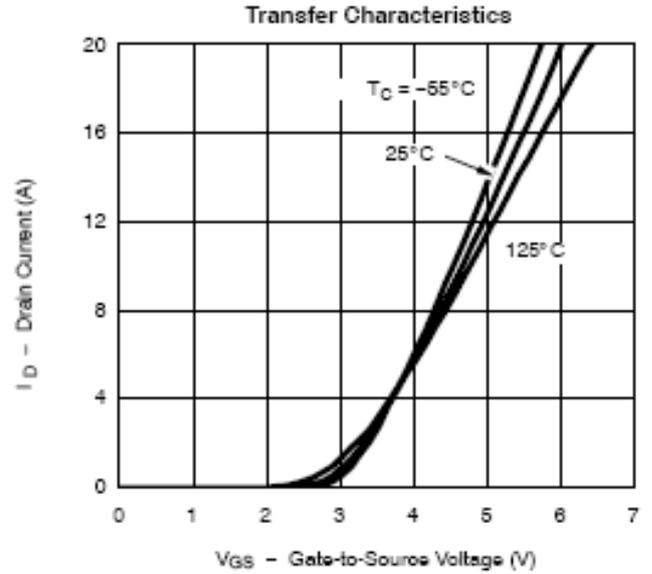
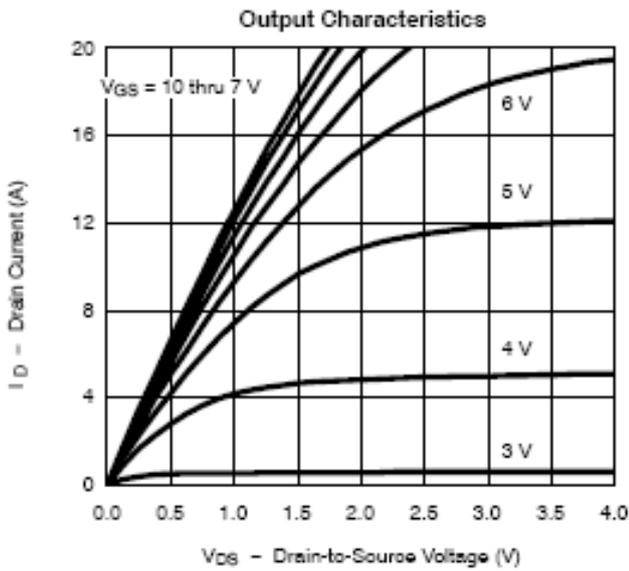
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.0		-3.0	
Gate Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 20V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-24V, V_{GS}=0V$			-1	uA
		$V_{DS}=-24V, V_{GS}=0V$ $T_J=85^\circ\text{C}$			-5	
On-State Drain Current	$I_{D(on)}$	$V_{DS}=-5V, V_{GS}=-4.5V$	-4			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-2.8A$		0.090	0.110	$\Omega$
		$V_{GS}=-4.5V, I_D=-2.5A$		0.125	0.140	
Forward Transconductance	$g_{fs}$	$V_{DS}=-10V, I_D=-2.8A$		4		S
Diode Forward Voltage	$V_{SD}$	$I_S=-1.2A, V_{GS}=0V$		-0.8	-1.2	V
<b>Dynamic</b>						
Total Gate Charge	$Q_g$	$V_{DS}=-15V, V_{GS}=-10V$ $I_D=-2.5A$		5.8	10	nC
Gate-Source Charge	$Q_{gs}$			0.8		
Gate-Drain Charge	$Q_{gd}$			1.5		
Input Capacitance	$C_{iss}$	$V_{DS}=-15V, V_{GS}=0V$ $f=1\text{MHz}$		226		pF
Output Capacitance	$C_{oss}$			87		
Reverse Transfer Capacitance	$C_{rss}$			19		
Turn-On Time	$t_{d(on)}$	$V_{DD}=-15V, R_L=15\Omega$ $I_D=-1.0A, V_{GEN}=-10V$ $R_G=6\Omega$		9	20	ns
	$t_r$			9	20	
Turn-Off Time	$t_{d(off)}$			18	35	
	$t_f$			6	20	



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### TYPICAL CHARACTERISTICS

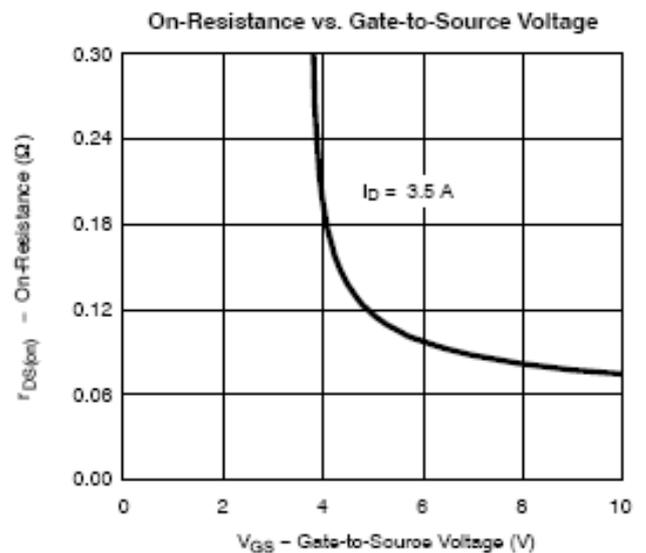
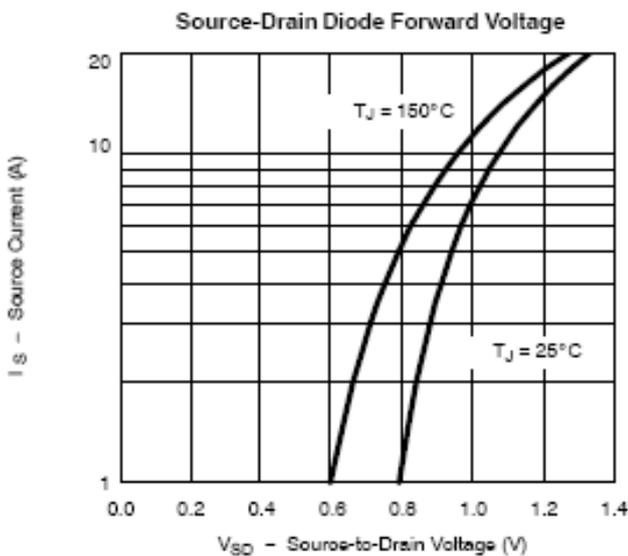
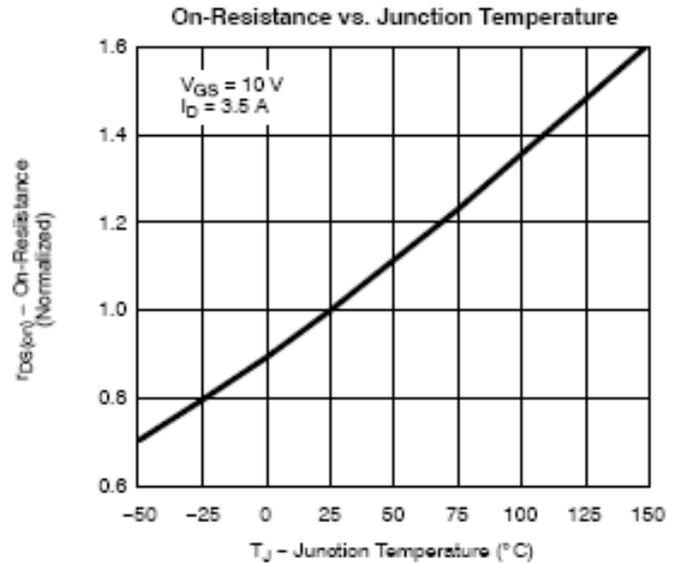
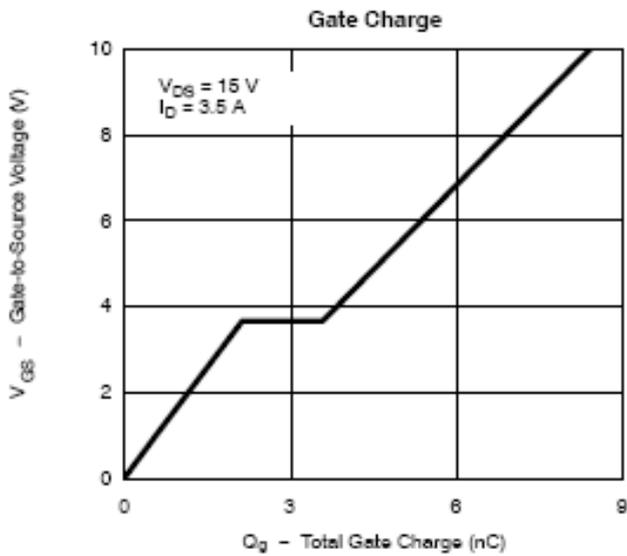




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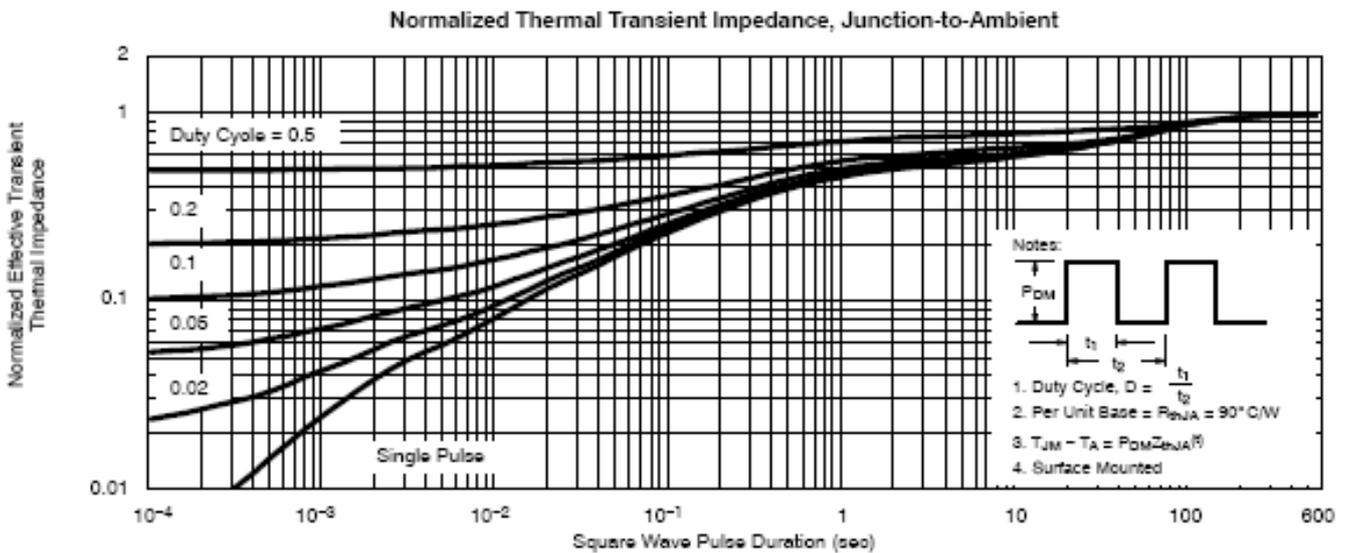
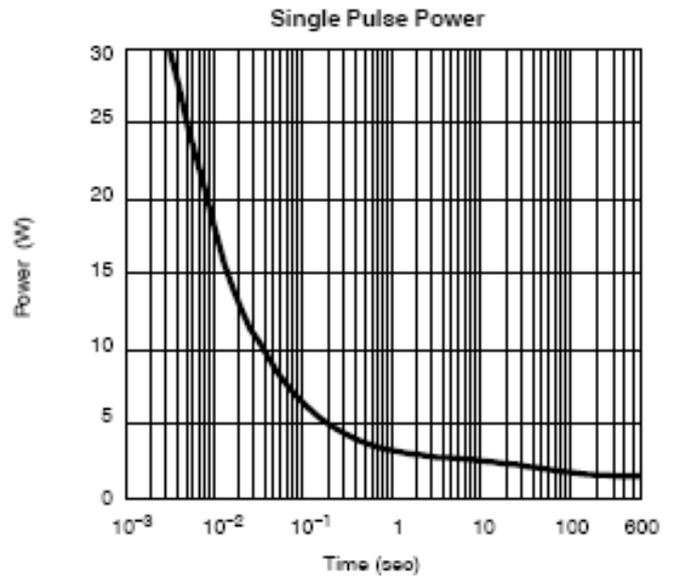
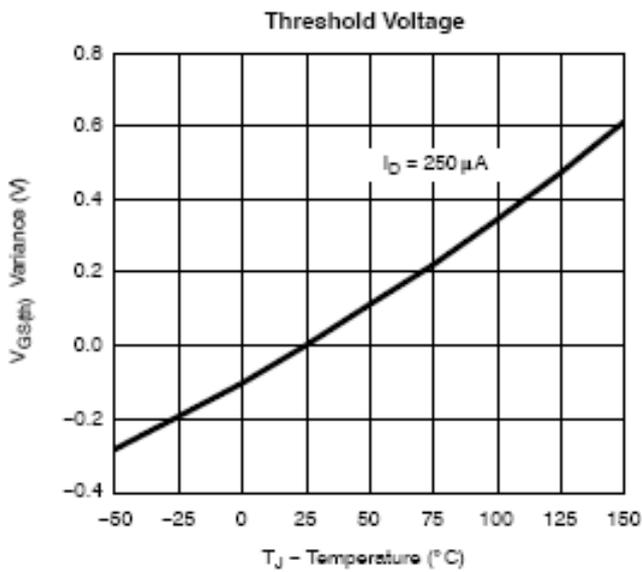
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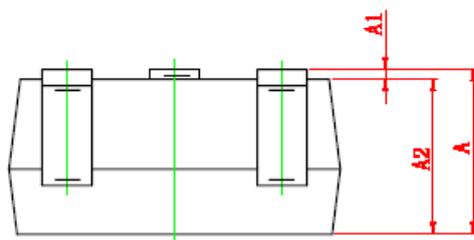
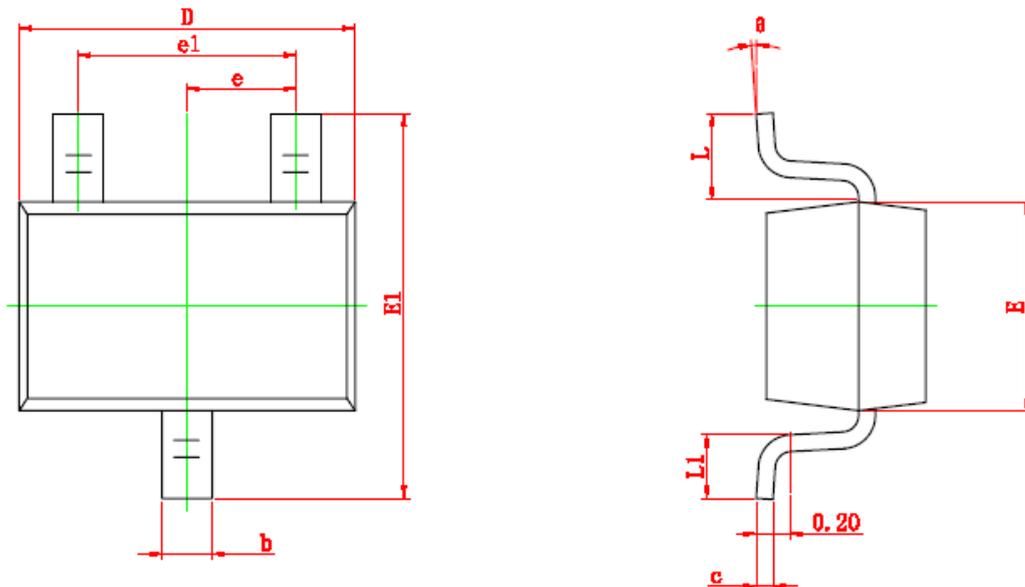




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### SOT-323 PACKAGE OUTLINE



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°



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